

**REMARKS**

Paragraphs [0002], [0017] and [0056] of the specification have been amended to correct minor typographical errors. Marked-up versions of amended paragraphs [0002], [0017] and [0056] are attached hereto as APPENDIX A. No new matter has been introduced by these amendments to the specification. Allowance of the application is solicited.

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Respectfully submitted,

By 

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## APPENDIX A

### Version With Markings to Show Changes Made

#### In the Specification:

[0002] CMOS active pixel sensors are known, and have been described, for example, in U.S. patent no. 5,471,515 [5,471,215]. CMOS active pixel sensors are often very small, in order to make them compatible with current elements. While the device includes an in-pixel follower and/or other in-pixel transistors, size miniaturization often prevents a full complementary MOS type switch. This means, therefore, that a full-scale reset function within the active pixel circuit may be difficult.

[0017] Figure 8 shows a row driver[s] circuit with separate boosting parts.

[0056] In the embodiment shown in figure 8, a separate boosting line [100] 800 is provided. The bodies of a plurality of switching transistors 805, [it] 810, 815 are connected to this dedicated boosting line. Using a [to read 0] boosting system as shown in figure 5[, ] allows the boost line [100] 800 to be used as the normal bootstrap circuit at the desired boosting level. A separate boost line 820 may be connected, and may be used to bring up the local body potential of certain transistors. This ensures that the local body potential will always be higher than the source line and the drain line of the switching transistors, even when a boosting voltage is applied.